Supplemental figures to the abstract

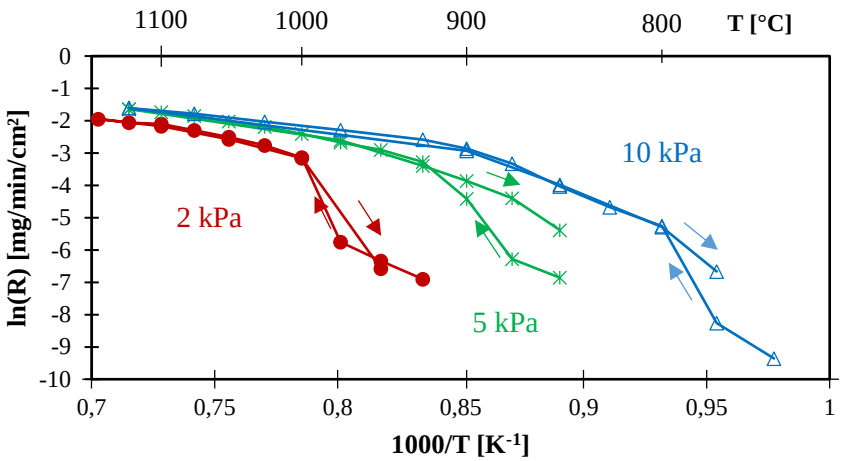


Fig. 1.a.: Arrhenius plots of the deposition rate R. $\alpha = 13$, $Q_{tot} = 150$ sccm.

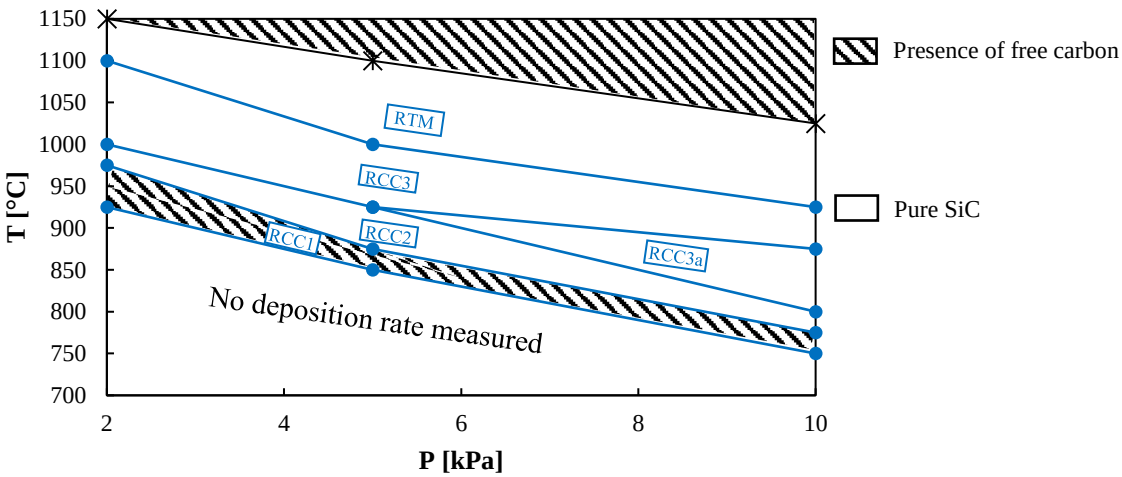


Fig. 1.b.: P-T diagram showing the different deposition regimes identified on the Arrhenius plots. $\alpha = 13$, $Q_{tot} = 150$ sccm.

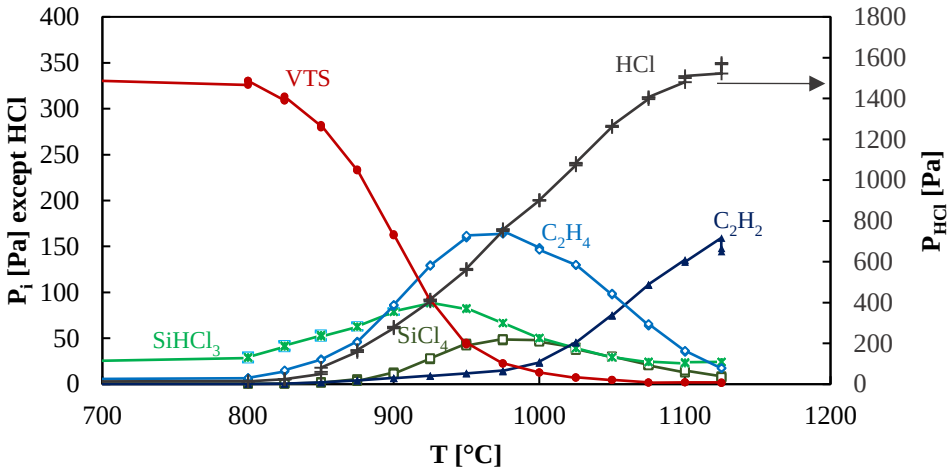


Fig. 2: Gas phase concentration, as measured by FTIR at the reactor outlet, as a function of temperature. P = 5 kPa, α = 13, Q_{tot} = 150 sccm.

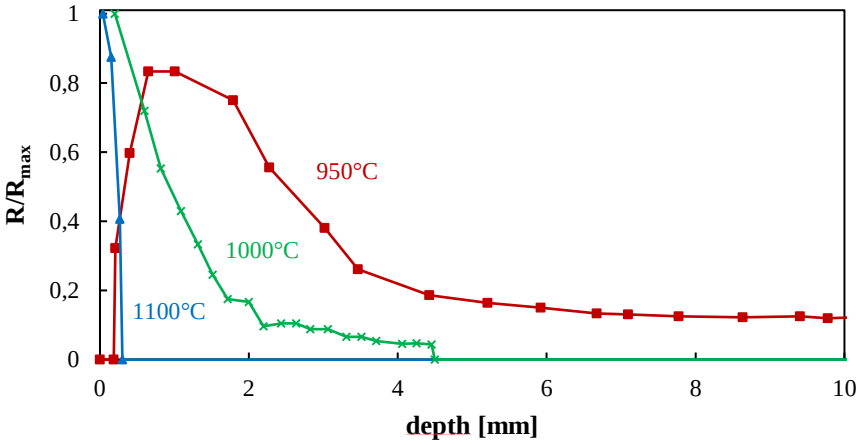


Fig. 3: Normalized deposition rate of pure SiC along the model channel pore (x = 0 mm at the entrance of a 100 µm-opening channel). P = 2 kPa, α = 13, Q_{tot} = 300 sccm.

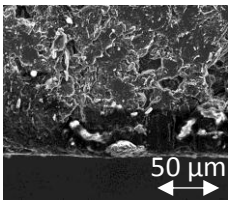
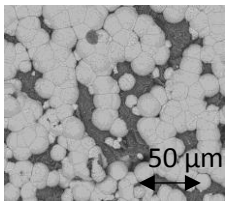
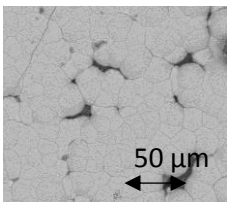
Position	0 mm	0,3 mm	1 mm
MEB image			
EDX analysis	C (at. %) = 97,3 Si (at. %) = 2,7	C (at. %) = 49,7 Si (at. %) = 50,3	C (at. %) = 49,3 Si (at. %) = 50,7

Fig. 4: SEM images of the porous substrates after CVI at T = 950°C, P = 2 kPa, α = 13, Q_{tot} = 300 sccm, at three different positions along the model channel pore (x = 0 mm at the entrance of the 100 µm-opening channel).